



TN0104N3-G-P014 Information



For Reference Only

Part Number TN0104N3-G-P014

Manufacturer Microchip Technology

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 40V 0.45A TO92-3 **Package** TO-226-3, TO-92-3 (TO-226AA)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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TN0104N3-G-P014 Specifications

Manufacturer Part Number TN0104N3-G-P014 Manufacturer Microchip Technology Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 450mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 3V, 10V Vgs(th) (Max) @ Id 1.6V @ 500μA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 70pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) IW (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-92-3, TO-92-3 (TO-226AA)		
Category Discrete Semiconductor Products Fackage TO-226-3, TO-92-3 (TO-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 450mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 3V, 10V Vgs(th) (Max) @ Id 1.6V @ 500μA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 70pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Manufacturer Part Number	TN0104N3-G-P014
Package To-226-3, To-92-3 (To-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 450mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 3V, 10V Vgs(th) (Max) @ Id 1.6V @ 500μA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 70pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) IW (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Manufacturer	Microchip Technology
Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 450mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 3V, 10V Vgs(th) (Max) @ Id 1.6V @ 500μA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 70pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) IW (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 450mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 3V, 10V Vgs(th) (Max) @ Id 1.6V @ 500μA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 70pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 (TO-226AA)		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) MOSFET (Metal Oxide) 40V Current - Continuous Drain (Id) @ 25°C 450mA (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) £20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature Mounting Type Supplier Device Package Package / Case N-Channel N-Channel NOSFET (Metal Oxide) AUV TOP 450mA (Ta) 3V, 10V 450mA 70P 20V 450mA 1.6V @ 500µA 1.6V @	Package	TO-226-3, TO-92-3 (TO-226AA)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C450mA (Ta)Drive Voltage (Max Rds On, Min Rds On)3V, 10VVgs(th) (Max) @ Id1.6V @ 500μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds70pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)1W (Tc)Rds On (Max) @ Id, Vgs1.8 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Series	-
Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C450mA (Ta)Drive Voltage (Max Rds On, Min Rds On)3V, 10VVgs(th) (Max) @ Id1.6V @ 500μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds70pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)1W (Tc)Rds On (Max) @ Id, Vgs1.8 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 450mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 3V, 10V Vgs(th) (Max) @ Id 1.6V @ 500μA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 70pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)3V, 10VVgs(th) (Max) @ Id1.6V @ 500μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds70pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)1W (Tc)Rds On (Max) @ Id, Vgs1.8 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Drain to Source Voltage (Vdss)	40V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 1.6V @ 500μA 1.6V @ 500μA 1.6V @ 500μA 1.6V @ 500μA 1.8 Ohm @ 20V 1.8 Ohm @ 1A, 10V 1	Current - Continuous Drain (Id) @ 25°C	450mA (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 70pF @ 20V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Drive Voltage (Max Rds On, Min Rds On)	3V, 10V
Input Capacitance (Ciss) (Max) @ Vds 70pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Vgs(th) (Max) @ Id	1.6V @ 500μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1W (Tc)Rds On (Max) @ Id, Vgs1.8 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Power Dissipation (Max) 1W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Input Capacitance (Ciss) (Max) @ Vds	70pF @ 20V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 1A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs1.8 Ohm @ 1A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Power Dissipation (Max)	1W (Tc)
Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Rds On (Max) @ Id, Vgs	1.8 Ohm @ 1A, 10V
Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-226-3, TO-92-3 (TO-226AA)	Mounting Type	Through Hole
	Supplier Device Package	TO-92-3
Report errors?	Package / Case	TO-226-3, TO-92-3 (TO-226AA)
		Report errors?

TN0104N3-G-P014 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TN0104N3-G-P014 Payment Methods





















TN0104N3-G-P014 Shipping Methods













If you have any question about TN0104N3-G-P014, please do not hesitate to contact us!

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